

L Number	Hits	Search Text	DB	Time stamp
1	488	etch\$3 near3 (resist photoresist) same ("o.sub.2" oxygen) same anisotropic	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/04/30 09:16
2	439	(etch\$3 near3 (resist photoresist) same ("o.sub.2" oxygen) same anisotropic) and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/04/30 09:17
3	5	("4472240" "5302477" "5635337" "6042996" "6171732").PN.	USPAT	2003/04/30 10:25
4	1524	438/706-710,725.ccls.	USPAT	2003/04/30 10:26
5	22	438/706-710,725.ccls. and tft	USPAT	2003/04/30 10:27
6	731	438/706-710,725.ccls. and etch\$3 near3 (resist photoresist)	USPAT	2003/04/30 10:27
7	306	438/706-710,725.ccls. and etch\$3 near3 (resist photoresist) same ("o.sub.2" oxygen)	USPAT	2003/04/30 10:28
8	807	((thin near film near transistor)) and 257/57,59.ccls.	USPAT	2003/04/30 10:37

L Number	Hits	Search Text	DB	Time stamp
1	488	etch\$3 near3 (resist photoresist) same ("o.sub.2" oxygen) same anisotropic	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/04/30 09:16
2	439	(etch\$3 near3 (resist photoresist) same ("o.sub.2" oxygen) same anisotropic) and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/04/30 09:17
3	5	("4472240" "5302477" "5635337" "6042996" "6171732").PN.	USPAT	2003/04/30 09:33
-	0	63-015472	USPAT; JPO; DERWENT	2002/12/17 09:01
-	2	"63015472"	USPAT; JPO; DERWENT	2002/12/17 09:04
-	1	1988-060121.NRAN.	DERWENT	2002/12/17 09:02
-	1	1988-060121.NRAN.	DERWENT	2002/12/17 09:03
-	1	1988-060121.NRAN.	DERWENT	2002/12/17 09:03
-	3	imashiro.in. and iida.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/12/17 09:05
-	6318	stanley near electric	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/12/17 09:05
-	62	(stanley near electric) and (thin near film near transistor)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/12/17 10:24
-	4	"314426"	EPO; JPO; DERWENT	2002/12/17 09:48
-	1	"5224186"	EPO; JPO; DERWENT	2002/12/17 09:48
-	1	"05228146"	EPO; JPO; DERWENT	2002/12/17 09:48
-	30120	(thin near film near transistor)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/12/17 10:29
-	947	257/57,59.ccls.	USPAT	2002/12/17 10:46
-	753	((thin near film near transistor)) and 257/57,59.ccls.	USPAT	2003/01/09 08:26
-	11	("5015597" "5355002" "5478766" "5693567" "5726077" "5757453" "6013930" "6028325" "6093580" "6122025" "6157426").PN.	USPAT	2002/12/17 11:48
-	7	("5471330" "5763301" "5767531" "5818067" "5861656" "6147667" "6246070").PN.	USPAT	2002/12/17 12:00
-	762	((thin near film near transistor)) and 257/57,59.ccls.	USPAT	2003/01/09 10:11
-	1	("5223914").PN.	USPAT	2003/01/09 10:20
-	147	438/717.ccls.	USPAT	2003/01/09 10:20
-	140	438/717.ccls. and (resist photoresist)	USPAT	2003/01/09 10:36
-	9	("5445710" "5843847" "5930677" "6087266" "6114259" "6211092" "6232134" "6294457" "6376366").PN.	USPAT	2003/01/09 10:21
-	13	("5356515" "5374332" "5399237" "5503901" "5578523" "5589041" "5595627" "5612254" "5635423" "5683548" "5741626" "5877075" "6043164").PN.	USPAT	2003/01/09 10:23
-	18	("5225035" "5237393" "5308721" "5328807" "5358827" "5384218" "5384219" "5414746" "5426010" "5446521" "5460908" "5477058" "5635337" "5635423" "5738757" "5741624" "5753417" "5821169").PN.	USPAT	2003/01/09 10:24

-	9	("4916511" "5091339" "5173442" "5264076" "5346586" "5466639" "5468342" "5567334" "5632908").PN.	USPAT	2003/01/09 10:25
-	2	("3518084" "5266446").PN.	USPAT	2003/01/09 10:29
-	6	("4231811" "4360586" "4890309" "5045417" "5135609" "5229255").PN.	USPAT	2003/01/09 10:31
-	9	("3920483" "3997367" "4035226" "4137458" "4140913" "4144101" "4149904" "4163155" "4182023").PN.	USPAT	2003/01/09 10:32
-	1	"5153083".PN.	USPAT	2003/01/09 10:35
-	1	("6444505").PN.	USPAT	2003/01/09 10:40
-	1	("6043164").PN.	USPAT	2003/01/09 10:41
-	10	("4472240" "4529860" "4950618" "5256583" "5259924" "5378309" "5492736" "5614765" "5635423" "5652182").PN.	USPAT	2003/01/09 10:48
-	10	((("6444505") or ("6043164") or ("5821169") or ("5308721") or ("5741624") or ("4231811") or ("5738757") or ("5384219") or ("6458284") or ("6200906"))).PN.	USPAT	2003/04/24 09:31
-	0	jp363015472	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/04/29 12:26
-	1	jp363015472A	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/04/29 12:26